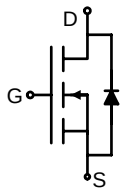
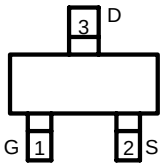
N-Channel Enhancement Mode Field Effect Transistor

FEATURE

- High dense cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability



Schematic diagram



R0 or AOH

Marking and pin Assignment

SOT-23 top view

Maximum ratings (T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	5.8	A
Drain Current-Pulsed (note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.38	W
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	90	℃/W
Thermal Resistance from Junction to Case (note 2)	$R_{\theta JC}$	30	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~+150	℃

Electrical characteristics (T_a=25℃ unless otherwise noted)

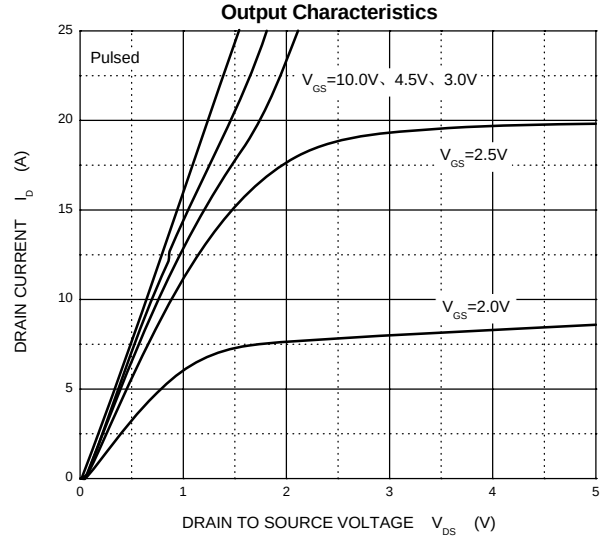
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	V_{GS} = 0V, I_D =250μA	30			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =24V,V_{GS} = 0V			1	μA
Gate-source leakage current	I_{GSS}	V_{GS} =±12V, V_{DS} = 0V			±100	nA
On characteristics						
Drain-source on-resistance (note 3)	$R_{DS(on)}$	V_{GS} =10V, I_D =5.8A			35	mΩ
		V_{GS} =4.5V, I_D =5A			40	mΩ
		V_{GS} =2.5V,I_D=4A			52	mΩ
Forward tranconductance	g_{FS}	V_{DS} =5V, I_D =5A	8			S
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.7		1.4	V
Dynamic Characteristics (note 4,5)						
Input capacitance	C_{iss}	V_{DS} =15V,V_{GS} =0V,f =1MHz			1050	pF
Output capacitance	C_{oss}			99		pF
Reverse transfer capacitance	C_{rss}			77		pF
Gate resistance	R_g	V_{DS} =0V,V_{GS} =0V,f =1MHz			3.6	Ω
Switching Characteristics (note 4,5)						
Turn-on delay time	$t_{d(on)}$	V_{GS}=10V,V_{DS}=15V, R_L=2.7Ω,R_{GEN}=3Ω			5	ns
Turn-on rise time	t_r				7	ns
Turn-off delay time	$t_{d(off)}$				40	ns
Turn-off fall time	t_f				6	ns
Drain-source diode characteristics and maximum ratings						
Diode forward voltage (note 3)	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note :

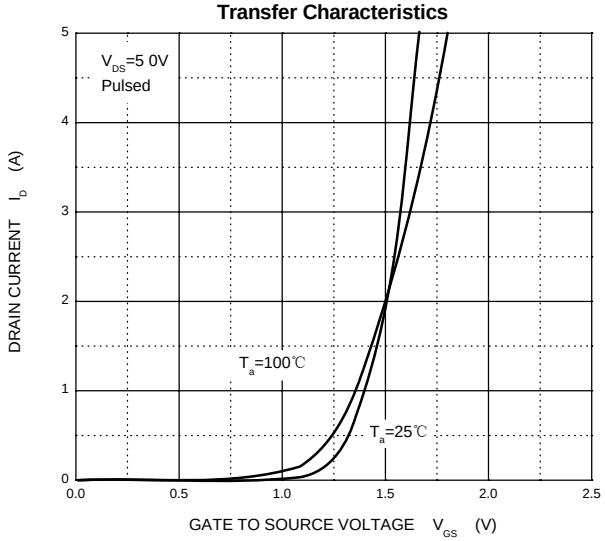
1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t < 5 sec.
3. Pulse Test : Pulse Width≤300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production testing.

Typical Characteristics

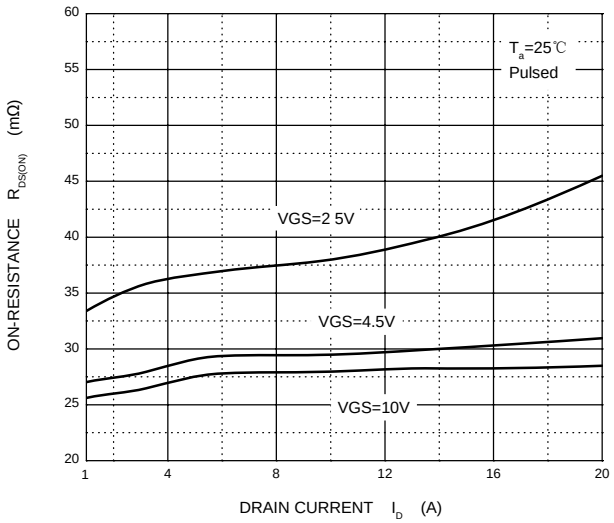
Output Characteristics



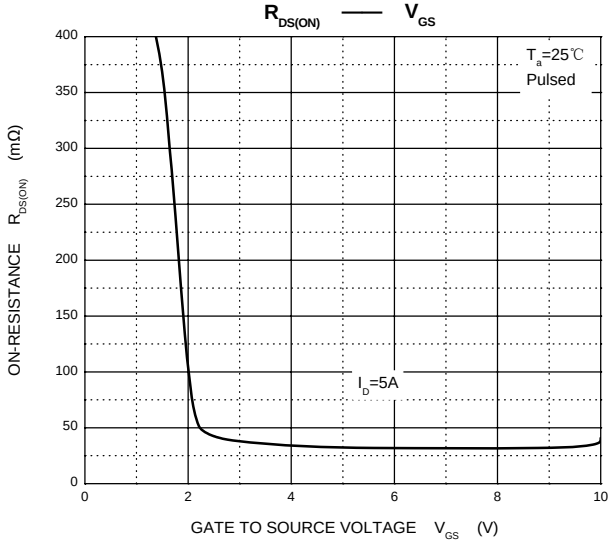
Transfer Characteristics



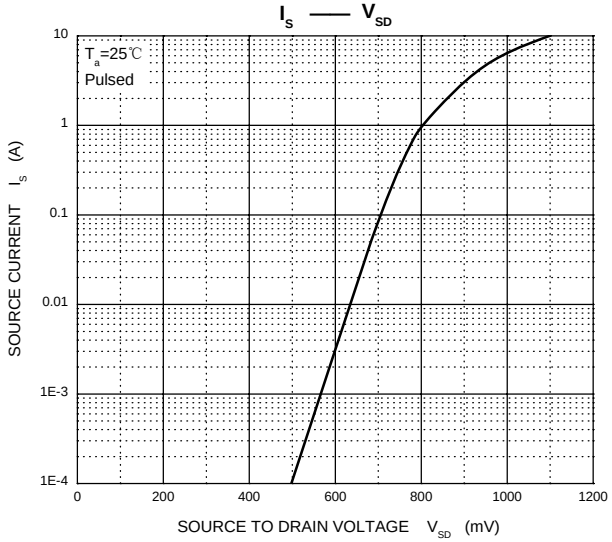
$R_{DS(ON)}$ —— I_D



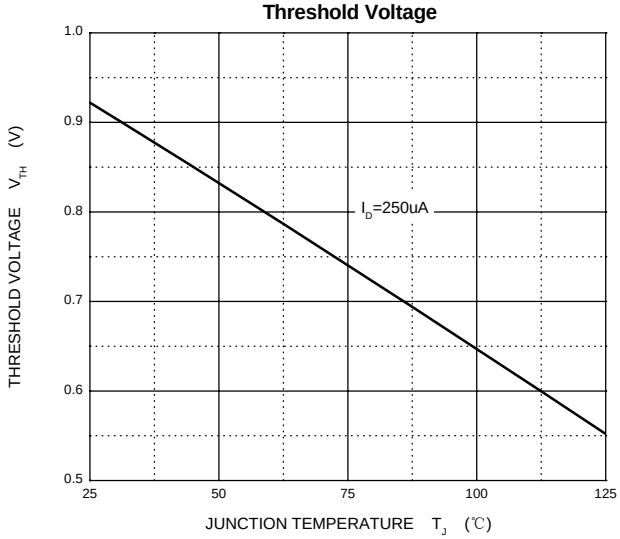
$R_{DS(ON)}$ —— V_{GS}



I_S —— V_{SD}

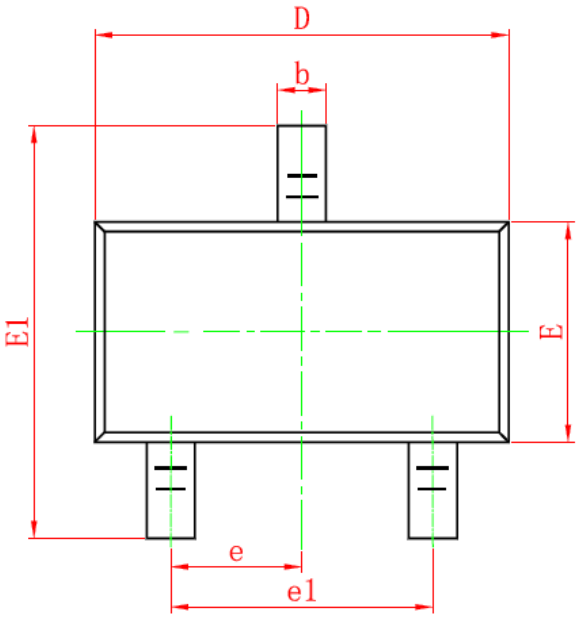


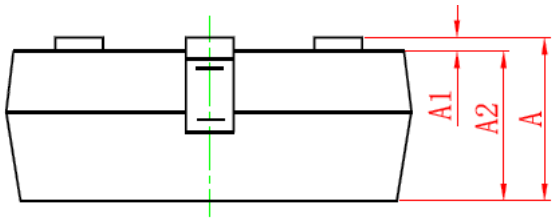
Threshold Voltage

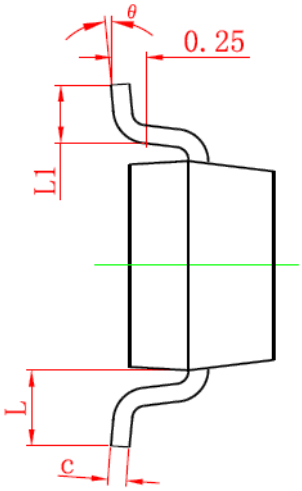


SOT-23 PACKAGE INFORMATION

Dimensions in Millimeters (UNIT:mm)







Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°

NOTES

1. All dimensions are in millimeters.
2. Tolerance ±0.10mm (4 mil) unless otherwise specified
3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
4. Dimension L is measured in gauge plane.
5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.